

<b>INFORMATION DISCLOSURE CITATION</b>  <b>PTO-1449</b>		<b>Atty. Docket No.</b> NMTI 1002-4	<b>Serial No.</b> 09/972,428-3974
		<b>Applicant</b> PIERRAT, Christophe	
		<b>Filing Date</b> 10/5/2001	<b>Group</b> <u>2824</u> <b>Not Yet Assigned</b>

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<u>JSR</u>	4,037,918	7/26/1977	Kato	350	3.5	7/31/1975
	4,456,371	6/26/1984	Lin	355	71	6/30/1982
	5,302,477	4/12/1994	Dao, et al.	430	5	8/21/1992
	5,308,741	5/3/1994	Kemp	430	312	7/31/1992
	5,316,878	5/31/1994	Saito, et al.	430	5	6/4/1992
	5,324,600	6/28/1994	Jinbo, et al.	430	5	7/7/1992
	5,328,807	7/12/1994	Tanaka, et al.	430	311	6/7/1991
	5,334,542	8/2/1994	Saito, et al.	437	40	11/18/1992
	5,352,550	10/4/1994	Okamoto	430	5	4/23/1993
	5,364,716	11/15/1994	Nakagawa, et al.	430	5	9/3/1992
	5,424,154	6/13/1995	Borodovsky	430	5	12/10/1993
	5,480,746	1/2/1996	Jinbo, et al.	430	5	5/16/1994
	5,496,666	3/5/1996	Chu, et al.	430	5	10/27/1994
	5,498,579	3/12/1996	Borodovsky, et al.	437	250	6/8/1994
	5,503,951	4/2/1996	Flanders, et al.	430	5	4/17/1995
	5,523,186	6/4/1996	Lin, et al.	430	5	12/16/1994
	5,527,645	6/18/1996	Pati, et al.	430	5	11/17/1994
	5,532,090	7/2/1996	Borodovsky	430	5	3/1/1995
	5,537,648	7/16/1996	Liebmann, et al.	395	500	8/15/1994
	5,538,815	7/23/1996	Oi, et al.	430	5	9/14/1993
	5,539,568	7/23/1996	Lin, et al.	359	285	6/7/1995
	5,565,286	10/15/1996	Lin	430	5	11/17/1994
<u>JSR</u>	5,573,890	11/12/1996	Spence	430	311	7/18/1994

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<u>JSP</u>	5,595,843	1/21/1997	Dao	430	5	3/30/1995
	5,620,816	4/15/1997	Dao	430	5	10/13/1995
	5,635,316	6/3/1997	Dao	430	5	10/13/1995
	5,636,131	6/3/1997	Liebmann, et al.	364	490	5/12/1995
	5,702,848	12/30/1997	Spence	430	5	8/23/1996
	5,725,969	3/10/1998	Lee	430	5	12/22/1995
	5,761,075	6/2/1998	Oi, et al.	364	488	5/31/1996
	5,766,804	6/16/1998	Spence	430	5	8/23/1996
	5,766,806	6/16/1998	Spence	430	5	9/9/1996
	5,807,649	9/15/1998	Liebmann, et al.	430	5	10/31/1996
	5,827,623	10/27/1998	Ishida, et al.	430	5	10/30/1996
	5,858,580	1/12/1999	Wang, et al.	430	5	9/17/1997
	5,885,734	3/23/1999	Pierrat, et al.	430	5	8/15/1996
	5,923,566	6/13/1999	Galan, et al.	364	489	3/25/1997
	5,994,002	11/30/1999	Matsuoka	430	5	9/4/1997
	5,998,068	12/7/1999	Matsuoka	430	5	1/27/1998
	6,004,702	12/21/1999	Lin	430	5	5/21/1998
	6,010,807	1/4/2000	Lin	430	5	4/7/1998
	6,057,063	5/2/2000	Liebmann, et al.	430	5	4/14/1997
	6,066,180	5/23/2000	Kim, et al.	716	19	3/15/1999
	6,077,630	6/20/2000	Pierrat	430	5	1/8/1998
	6,083,275	7/4/2000	Heng, et al.	716	19	1/9/1998
<u>JSP</u>	6,228,539 B1	5/8/2001	Wang, et al.	430	5	1/12/1999

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<i>JSL</i>	6,251,549 B1	6/26/2001	Levenson	430	11	10/28/1999
<i>JSL</i>	6,258,493 B1	7/10/2001	Wang, et al.	430	5	7/17/2000

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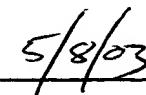
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						YES	NO
JSR	JP 6-67403	3/11/1994	JP			<input checked="" type="checkbox"/>	<input type="checkbox"/>
	0 698 821	2/28/1996	EPO			<input type="checkbox"/>	<input type="checkbox"/>
JSR	8-51068	2/20/1996	JP			<input checked="" type="checkbox"/>	<input type="checkbox"/>
	2,638,561	4/25/1997	JP			<input type="checkbox"/>	<input type="checkbox"/>
	2,650,962	5/16/1997	JP			<input type="checkbox"/>	<input type="checkbox"/>
JSR	EP 0 464 492 A1	1/8/1992	EP			<input type="checkbox"/>	<input type="checkbox"/>
	EP 0 653 679 A2	5/17/1995	EP			<input type="checkbox"/>	<input type="checkbox"/>
	7-111528	2/14/1991	JP			<input type="checkbox"/>	<input type="checkbox"/>
JSR	8-236317	9/6/1996	JP			<input type="checkbox"/>	<input type="checkbox"/>
	10 133356	5/22/1998	JP			<input type="checkbox"/>	<input type="checkbox"/>
	11-143085	5/28/1999	JP			<input type="checkbox"/>	<input type="checkbox"/>
JSR	JP 62067547	3/27/1987	JP			<input type="checkbox"/>	<input type="checkbox"/>
	DE 195 43 163 A1	6/3/1996	DE			<input type="checkbox"/>	<input type="checkbox"/>

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<i>JSP</i>	Morikawa, Y., et al., "100nm-alt.PSM Structure Discussion for ArF Lithography", Dai-Nippon Printing Co., Ltd. (15 pages).		

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	Fukuda, H., et al., "Patterning of Random Interconnect Using Double Exposure of Strong-Type PSMs", Hitachi Central Research Lab (8 pages).		
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<b>INFORMATION DISCLOSURE CITATION</b>  <b>PTO-1449</b>		<b>Atty. Docket No.</b> NMTI 1002-4	<b>Serial No.</b> 09/972,428-3974
		<b>Applicant</b> PIERRAT, Christophe	
		<b>Filing Date</b> 10/5/2001	<b>Group</b> <u>2824</u> <b>Not Yet Assigned</b>
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						YES	NO
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	WO 02/03140 A1	1/10/2002	WO			<input type="checkbox"/>	<input type="checkbox"/>
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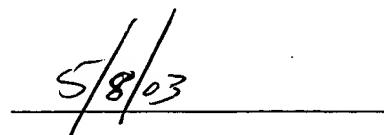
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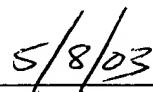
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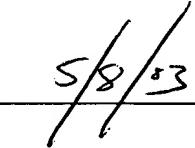
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						YES	NO
<i>JSR</i>	WO 02/073312 A1	9/19/2002	WO			<input type="checkbox"/>	<input type="checkbox"/>

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